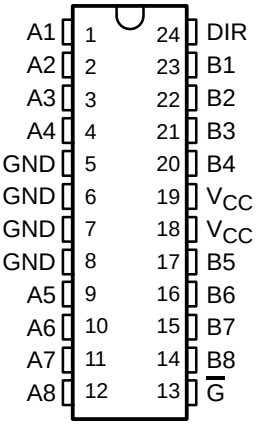
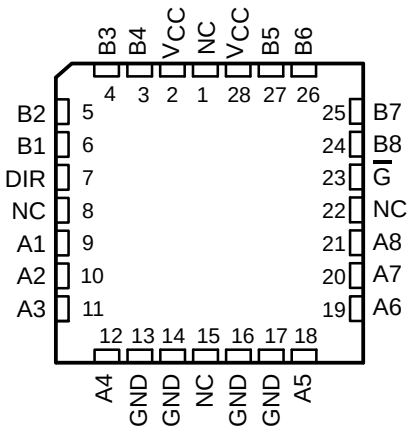
- **Bidirectional Bus Transceivers in High-Density 24-Pin Packages**
- **Inputs Are TTL-Voltage Compatible**
- **Flow-Through Architecture to Optimize PCB Layout**
- **Center-Pin V_{CC} and GND Configurations to Minimize High-Speed Switching Noise**
- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) 1-μm Process**
- **500-mA Typical Latch-Up Immunity at 125°C**
- **Package Options Include Plastic Small-Outline Packages, Ceramic Chip Carriers, and Standard Plastic and Ceramic 300-mil DIPs**

54ACT11640 . . . JT PACKAGE
74ACT11640 . . . DW OR NT PACKAGE
(TOP VIEW)



54ACT11640 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal bus transceivers are designed for asynchronous two-way communication between data buses. These devices transmit data from the A bus to the B bus or from the B bus to the A bus depending upon the level at the direction control (DIR) input. The enable input $\overline{G}$ is used to disable the device so the buses are effectively isolated.

The 54ACT11640 is characterized for operation over the full military temperature range of –55°C to 125°C. The 74ACT11640 is characterized for operation from – 40°C to 85°C.

FUNCTION TABLE

CONTROL INPUTS		OPERATION
$\overline{G}$	DIR	
L	L	$\overline{B}$ data to A bus
L	H	$\overline{A}$ data to B bus
H	X	Isolation

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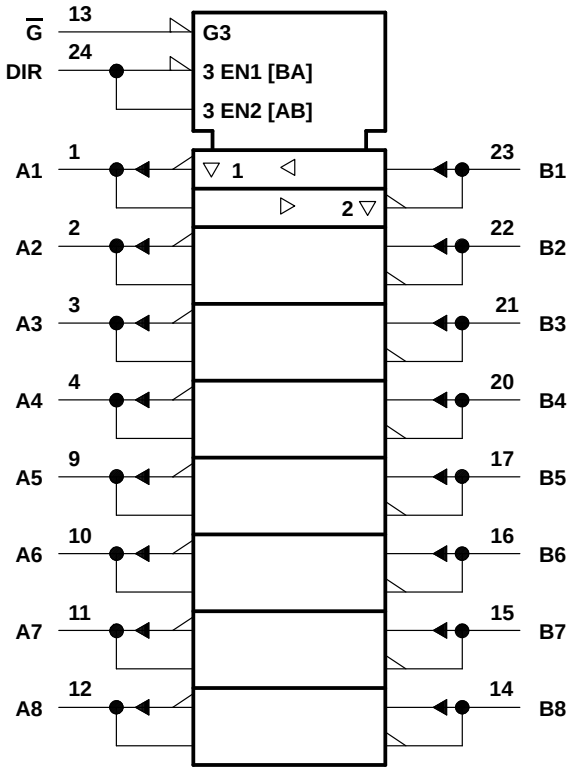
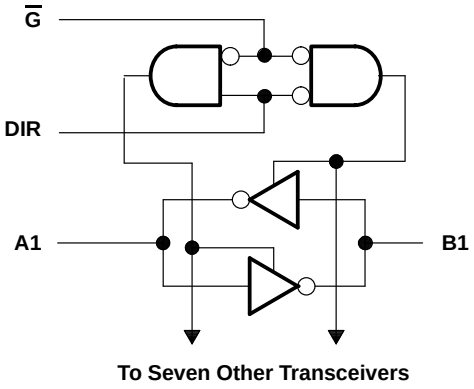
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DW, JT, and NT packages.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} . . . . . –0.5 V to 6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) . . . . . ± 20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ± 50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ± 50 mA
Continuous current through V_{CC} or GND . . . . . ± 200 mA
Storage temperature range . . . . . –65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTE 1: The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

recommended operating conditions

		54ACT11640			74ACT11640			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage	4.5	5	5.5	4.5	5	5.5	V
V_{IH}	High-level input voltage	2			2			V
V_{IL}	Low-level input voltage			0.8			0.8	V
V_I	Input voltage	0		V_{CC}	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	0		V_{CC}	V
I_{OH}	High-level output current			–24			–24	mA
I_{OL}	Low-level output current			24			24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0		10	0		10	ns/V
T_A	Operating free-air temperature	–55		125	– 40		85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = 25°C			54ACT11640		74ACT11640		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}		I_{OH} = – 50 μA	4.5 V	4.4			4.4		4.4		V
			5.5 V	5.4			5.4		5.4		
		I_{OH} = – 24 mA	4.5 V	3.94			3.7		3.8		
			5.5 V	4.94			4.7		4.8		
		I_{OH} = – 50 mA†	5.5 V				3.85				
		I_{OH} = – 75 mA†	5.5 V						3.85		
V_{OL}		I_{OL} = 50 μA	4.5 V			0.1		0.1		0.1	V
			5.5 V			0.1		0.1		0.1	
		I_{OL} = 24 mA	4.5 V			0.36		0.5		0.44	
			5.5 V			0.36		0.5		0.44	
		I_{OL} = 50 mA†	5.5 V					1.65			
		I_{OL} = 75 mA†	5.5 V							1.65	
I_{OZ}	A or B ports‡	$V_O = V_{CC}$ or GND	5.5 V			± 0.5		± 10		± 5	μA
I_I	$\overline{G}$ or DIR	$V_I = V_{CC}$ or GND	5.5 V			± 0.1		± 1		± 1	μA
I_{CC}		$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			8		160		80	μA
ΔI_{CC}§		One input at 3.4 V, Other inputs at GND or V_{CC}	5.5 V			0.9		1		1	mA
C_i	$\overline{G}$ or DIR	$V_I = V_{CC}$ or GND	5 V		4						pF
C_{io}	A or B ports	$V_O = V_{CC}$ or GND	5 V		12						pF

† Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

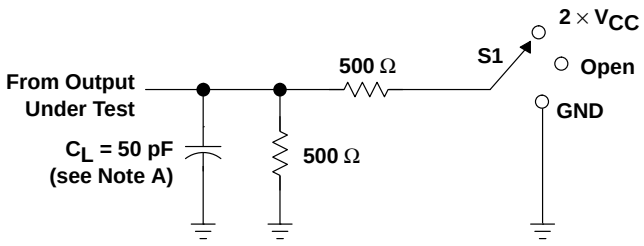
switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = 25°C			54ACT11640		74ACT11640		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.5	6.3	9.6	1.5	11	1.5	10.5	ns
t_{PHL}			1.5	5.7	8.6	1.5	10	1.5	9.5	
t_{PZH}	$\overline{G}$	A or B	1.5	8.8	12.2	1.5	14.2	1.5	13.4	ns
t_{PZL}			1.5	8.4	12.3	1.5	14.5	1.5	13.6	
t_{PHZ}	$\overline{G}$	A or B	1.5	9.1	12.9	1.5	14.5	1.5	13.9	ns
t_{PLZ}			1.5	9.6	13.1	1.5	15	1.5	14.2	

operating characteristics, V_{CC} = 5 V, T_A = 25°C

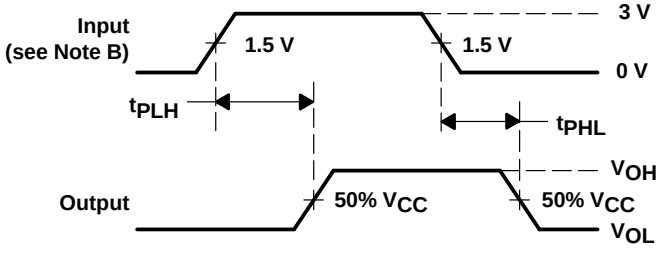
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF,	f = 1 MHz	45	pF
		Outputs disabled			12	

PARAMETER MEASUREMENT INFORMATION

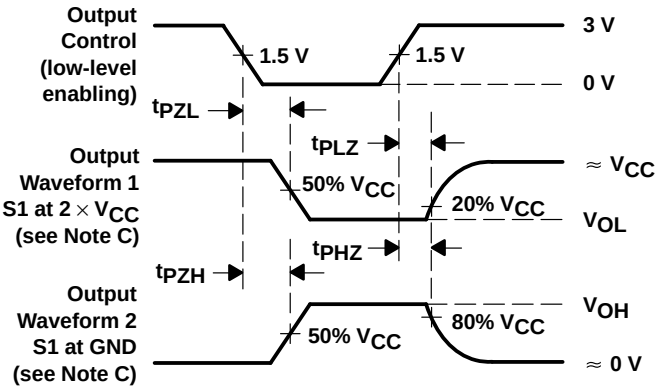


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

LOAD CIRCUIT



VOLTAGE WAVEFORMS



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r = 3 ns, t_f = 3 ns.
C. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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